

C850DS-100

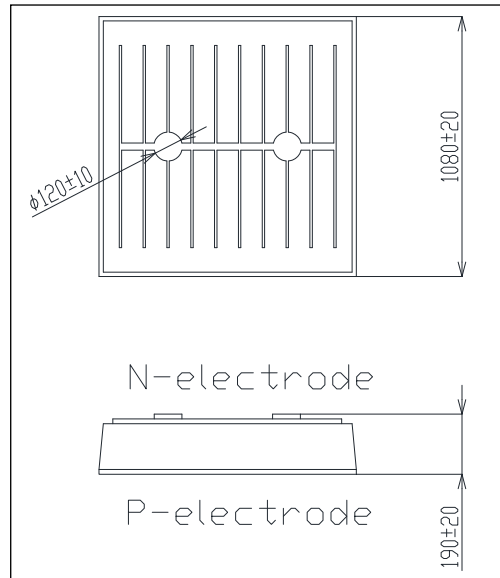
PRELIMINARY

High Power LED Chip

<Specifications>

- Material: AlGaAs
- p-pad Electrode: Au Alloy
- n-pad Electrode: Au Alloy
- Chip Size: 1080 μ m x 1080 μ m typical
- Chip Thickness: 190 μ m typical
- Pad Diameter: Φ 120 μ m typical

Outline and Internal Circuit (Unit: μ m)

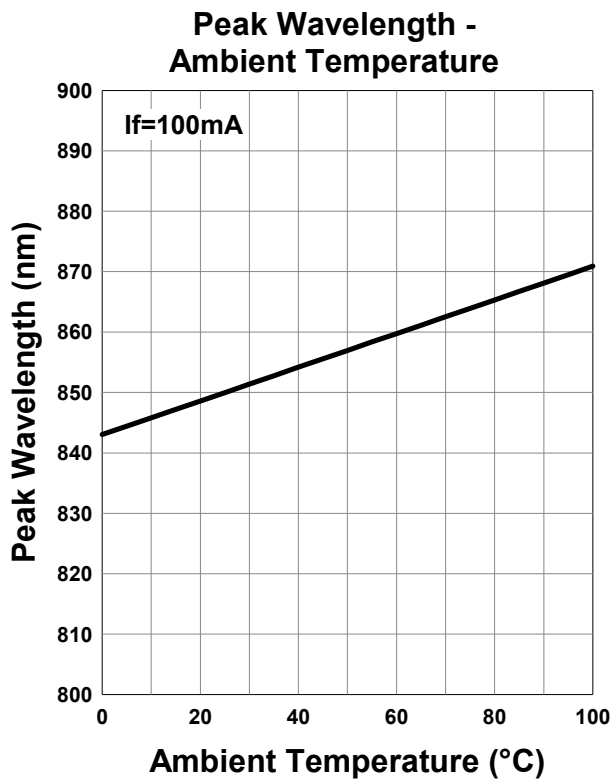
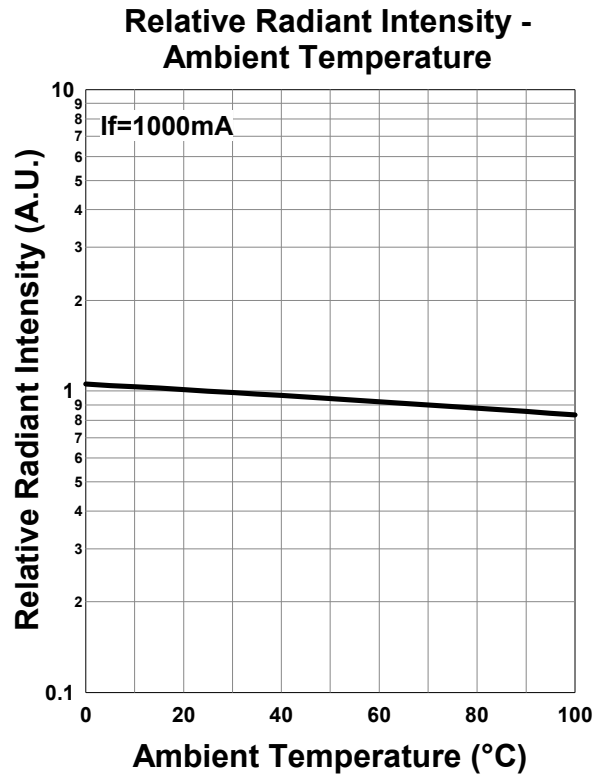
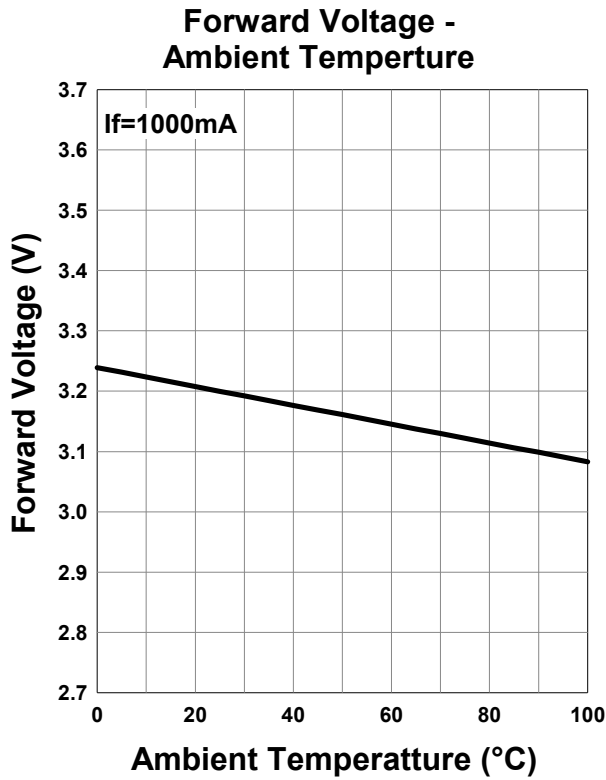


Absolute Maximum Ratings[Ta=25°C]			
Item	Symbol	Ratings	Unit
Power Dissipation	PD	4200	mW
Forward Current	IF	1000	mA
Pulse Forward Current*	IFP	(5000)	mA
Reverse Voltage	VR	5	V
Junction Temperature	Tj	120	°C

* Duty 1% and Pulse Width=10us

Electro-Optical Characteristics [Ta=25°C]						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=1A		(3.2)	4.2	V
Reverse Current	IR	VR=5V			10	uA
Total Radiated Power	PO	IF=1A	600			mW
Peak Wavelength	λ P	IF=100mA	(820)	850	(880)	nm

Die shall be mounted on TO-46 gold header without resin coated.



Disclaimer

Product specifications and data shown in this product catalog are subject to change without notice for the purposes of improving product performance, reliability, design, or otherwise.

Product data and parameters in this catalog are typical values based on reasonably up-to-date measurements.

Product data and parameters may vary by user application and over time.

Products shown in this catalog are intended to be used for general electronic equipment. Products are not guaranteed for applications where product malfunction or failure may cause personal injury or death, including but not limited to life-supporting / saving devices, medical devices, safety devices, airplanes, aerospace equipment, automobiles, traffic control systems, and nuclear reactor control systems.

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